

Pending

Active

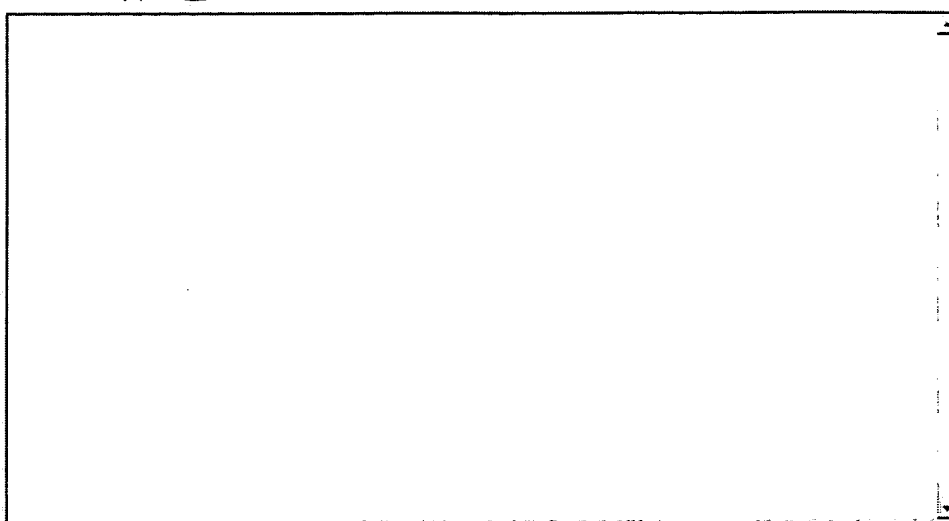
- ☒ L1: (55) (electron near2 emission) and (electrode near2 (lower and upper and counter))
- ☒ L2: (33) 1 and (semiconductor near2 (layer or film or coatS3))
- ☒ L3: (33) 2 and (voltage or potential)
- ☒ L5: (73) 4 and (semiconductor near2 (layer or film or coatS3))
- ☒ L6: (71) 5 and (voltage or potential)
- ☒ L14: (128) 4 and (voltage or potential)
- ☒ L4: (132) (electron near2 emiS5) and (electrode near2 (lower and upper and counter))
- ☒ L31: (4979) (electron near2 emiS5) and electrode and (semiconductor near2 (film or coatS3 or layer)) and (voltage or potential)
- ☒ L32: (20) 31 and (cleaning near2 functionS3)
- ☒ L33: (452) (electron near2 emiS5) and (electrode near2 (upper and lower)) and (semiconductor near2 (film or coatS3 or layer)) and (voltage or potential)
- ☒ L34: (70) 33 and (counter adj electrode)
- ☒ L36: (27) (electron near2 emiS5) and (electrode near2 (upper and lower and counter)) and "313"/S.ccls.
- ☒ L35: (691) (electron near2 emiS5) and (electrode near2 (upper and lower)) and "313"/S.ccls.

- ☐ Failed
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- ☐ Queue
- ☐ Trash

Search List Browse Queue Clear

DBs US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB

Default operator: OR

☒ Plurals☒ Highlight all hit terms initially

BRS form IS&R form Image Text HTML

	Type	L #	Hits	Search Text	DBs	Time Stamp	C	Er	Erro
1	BRS	L1	55	(electron near2 emission) and (electrode near2 (lower and upper and counter))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:00			
2	BRS	L2	33	1 and (semiconductor near2 (layer or film or coatS3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:00			
3	BRS	L3	33	2 and (voltage or potential)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:00			
4	BRS	L5	73	4 and (semiconductor near2 (layer or film or coatS3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:00			
5	BRS	L6	71	5 and (voltage or potential)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:11			
6	BRS	L14	128	4 and (voltage or potential)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:24			
7	BRS	L4	132	(electron near2 emiS5) and (electrode near2 (lower and upper and counter))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:34			
8	BRS	L31	4979	(electron near2 emiS5) and electrode and (semiconductor near2 (film or coatS3 or layer)) and (voltage or potential)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:38			
9	BRS	L32	20	31 and (cleaning near2 functionS3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:36			
10	BRS	L33	452	(electron near2 emiS5) and (electrode near2 (upper and lower)) and (semiconductor near2 (film or coatS3 or layer)) and (voltage or potential)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:48			
11	BRS	L34	70	33 and (counter adj electrode)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:44			
12	BRS	L36	27	(electron near2 emiS5) and (electrode near2 (upper and lower and counter)) and "313"/S.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:49			
13	BRS	L35	691	(electron near2 emiS5) and (electrode near2 (upper and lower)) and "313"/S.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	2006/12/04 14:50			

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